

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	22	((BERNARD) near2 (BECHEVET)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:09
S1	1	((PETER) near2 (HARING-BOLIVAR)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:09
S3	9	((VERONIQUE) near2 (SOUSA)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:10
S6	1	((FLORIAN) near2 (MERGET)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:11
S5	17	((HEINRICH) near2 (KURZ)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:11
S4	1	((DAE-HWANG) near2 (KIM)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:11
S8	5	US-6854033-\$.DID. OR US-7214632-\$.DID. OR US-7227171-\$.DID. OR US-7358521-\$.DID. OR US-20080002457-\$.DID.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:14
S7	9	US-3448302-\$.DID. OR US-4420766-\$.DID. OR US-4599705-\$.DID. OR US-4795657-\$.DID. OR US-5049971-\$.DID. OR US-6087689-\$.DID. OR US-6287887-\$.DID. OR US-6473332-\$.DID.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:14
S9	2	US-5933365-\$.DID. OR US-6525953-\$.DID.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:19
S10	44372	PCM or (phase adj change adj memory) or PRAM or PCRAM or (phase adj chang\$5 adj RAM) or (programmable adj conductor adj (RAM or memory)) or (programmable adj resistance adj2 element) or C-RAM or (Chalcogenide adj RAM) or OUM or (Ovonic adj Unified adj Memory)	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:38
S11	9	(lateral\$4 or horizon\$3) adj2 switch\$4 adj2 zone	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:39
S13	2	S10 same S12	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:40

S12	2233	switch\$4 adj2 zone	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:40
S14	30	S10 and S12	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:41
S16	3	S12 same S15	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:42
S15	19647	memory adj2 material	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:42
S17	28	S14 not S13	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 16:47
S18	2774	365/163,148,100.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 17:21
S19	2	S12 and S18	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 17:22
S21	3	S12 same S20	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 17:23
S20	6713	memory adj2 (layer)	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/14 17:23
S22	26	electrode with S12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 17:24
S25	26	S15 and S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:00
S24	0	S12 and S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:00
S23	7451	257/52-63.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:00
S26	2129	257/2-5.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:06

S27	3	S26 and S12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/14 19:07
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EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S30	4536	(memory adj2 material). clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:03
S29	324	(switch\$4 adj2 zone).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:03
S28	1	((lateral\$4 or horizon\$3) adj2 switch\$4 adj2 zone). clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:03
S32	25	memory same S29	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:04
S31	1	S29 and S30	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:04
S33	8	electrode same S29	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:05
S34	2793	365/163,148,100.ccls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:06
S36	5836	257/52-63.ccls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:07
S35	2123	257/2-5.ccls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:07
S39	5315	(PCM or (phase adj change adj memory) or PRAM or PCRAM or (phase adj chang \$5 adj RAM) or (programmable adj conductor adj (RAM or memory)) or (programmable adj resistance adj2 element) or C-RAM or (Chalcogenide adj RAM) or OUM or (Ovonic adj Unified adj Memory)).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:08

S38	318	S30 and (S34 or S35 or S36)	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:08
S37	3	S29 and (S34 or S35 or S36)	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:08
S40	97	S38 and S39	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/14 19:09
L10	3	8 and 9	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 08:41
L9	5315	(PCM or (phase adj change adj memory) or PRAM or PGRAM or (phase adj chang \$5 adj RAM) or (programmable adj conductor adj (RAM or memory)) or (programmable adj resistance adj2 element) or C-RAM or (Chalcogenide adj RAM) or OUM or (Ovonic adj Unified adj Memory)).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 08:41
L8	1052	(switch\$4 adj2 area).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 08:41
L11	69	electrode same L8	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 08:43
L14	1	8 and 13	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:07
L13	4536	(memory adj2 material).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:07
L19	4	8 and 18	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08
L18	10333	15 or 16 or 17	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08
L17	2793	365/163,148,100.ccls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08
L16	2123	257/2-5.ccls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08
L15	5836	257/52-63.ccls.	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:08

L21	208	18 and 20	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:09
L20	801	switch\$4 same 9	US-PGPUB; USPAT; UPAD	OR	ON	2010/09/15 09:09

9/ 15/ 10 10:03:28 AM

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